



2SB1260

PNP EPITAXIAL SILICON TRANSISTOR

POWER TRANSISTOR

DESCRIPTION

The UTC 2SB1260 is a epitaxial planar type PNP silicon transistor.

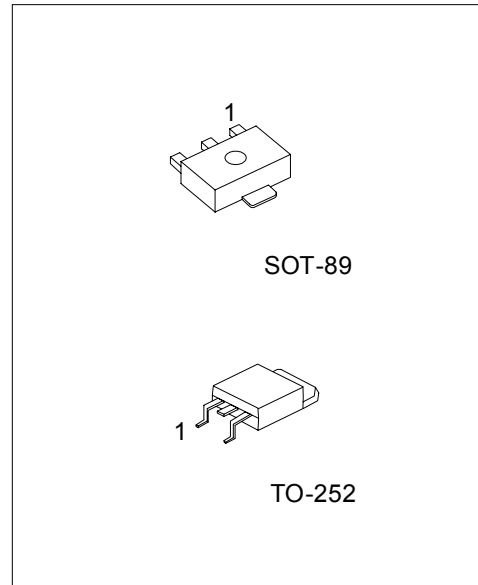
FEATURES

*High breakdown voltage and high current.

$BV_{CEO} = -80V$, $I_C = -1A$

*Good h_{FE} linearity.

*Low $V_{CE(SAT)}$



*Pb-free plating product number: 2SB1260L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SB1260-x-AB3-F-R	2SB1260L-x-AB3-F-R	SOT-89	B	C	E	Tape Reel
2SB1260-x-TN3-F-R	2SB1260L-x-TN3-F-R	TO-252	B	C	E	Tape Reel
2SB1260-x-TN3-F-T	2SB1260L-x-TN3-F-T	TO-252	B	C	E	Tube

<p>2SB1260L-x-AB3-F-R</p>	<p>(1) Packing Type (2) Pin Assignment (3) Package Type (4) Rank (5) Lead Plating</p> <p>(1) B: Tape Box, K: Bulk, R: Tape Reel (2) refer to Pin Assignment (3) AB3: SOT-89, TN3: TO-252 (4) refer to Classification of h_{FE} (5) L: Lead Free Plating, Blank: Pb/Sn</p>
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■ **ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector -Base Voltage	V _{CBO}	-80	V
Collector -Emitter Voltage	V _{CEO}	-80	V
Emitter -Base Voltage	V _{EBO}	-5	V
Peak Collector Current (single pulse, Pw=100ms)	I _{CM}	-2	A
DC Collector Current	I _C	-1	A
Power Dissipation	SOT-89	0.5	W
	TO-252	1.9	W
Operating Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note 1. Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (Ta= 25°C, unless otherwise specified)

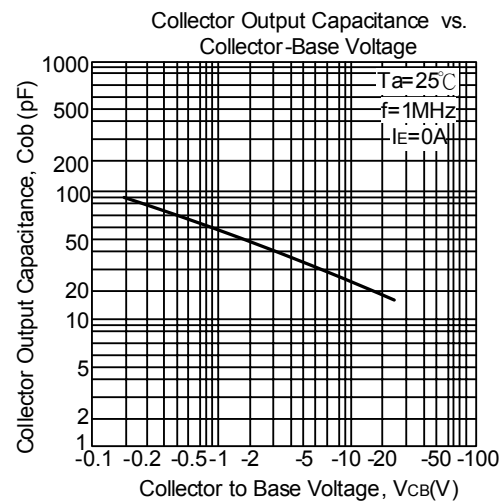
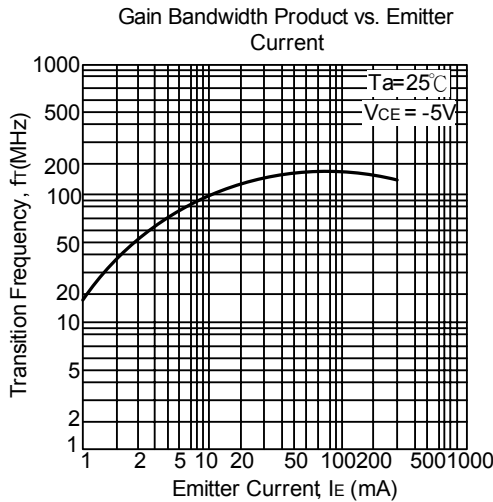
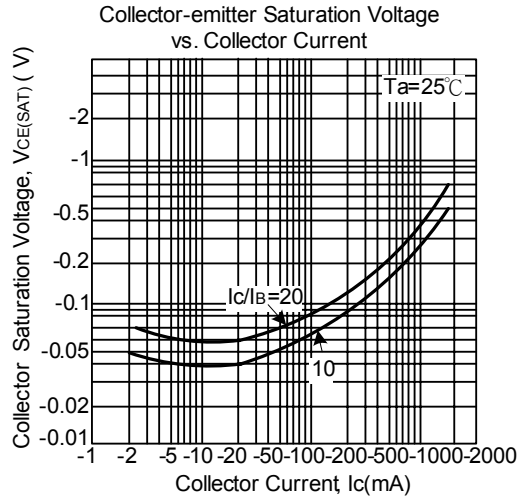
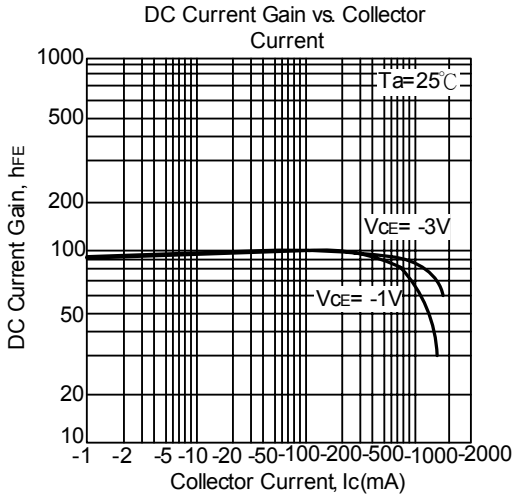
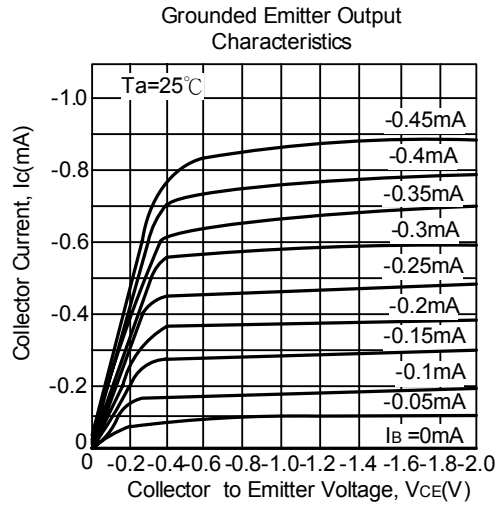
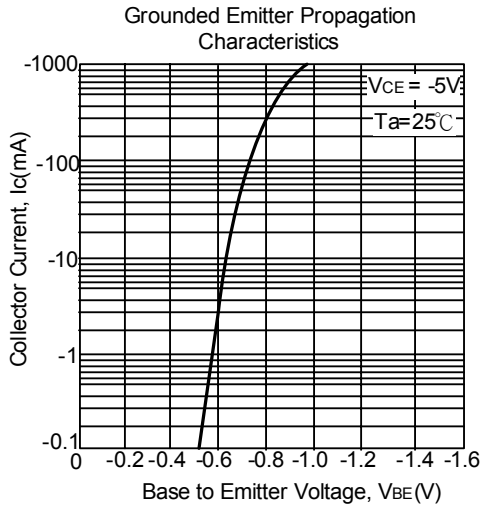
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV _{CBO}	I _C = -50 μA	-80			V
Collector Emitter Breakdown Voltage	BV _{CEO}	I _C = -1mA	-80			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E = -50 μA	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-60V			-1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-4V			-1	μA
DC Current Gain(Note 1)	h _{FE}	V _{CE} =-3V, I _{OUT} =-0.1A	82		390	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-0.4	V
Transition Frequency	f _T	V _{CE} = -5V, I _E =50mA, f=30MHz		100		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		25		pF

Note 1: Pulse test: P_w<300μs, Duty Cycle<2%

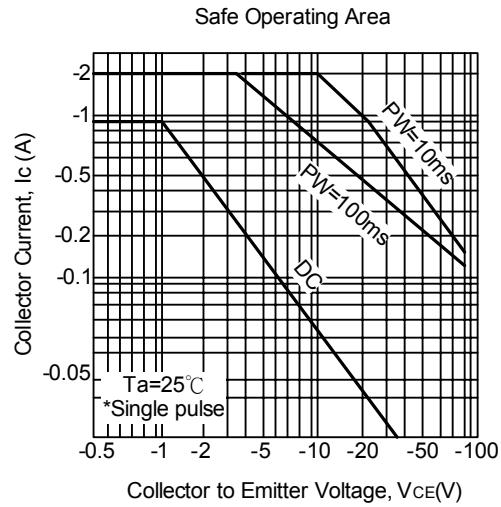
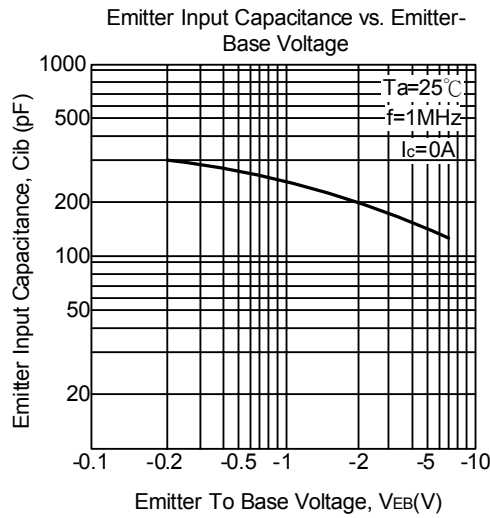
■ **CLASSIFICATION OF h_{FE}**

RANK	P	Q	R
RANGE	82 ~ 180	120 ~ 270	180 ~ 390

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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